

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		<i>Complete If Known</i>			
		Application Number	10/6/4,553		
		Filing Date	Concurrently Herewith		
		First Named Inventor	Edouard D. de Fresart		
		Group Art Unit	2823		
		Examiner Name			
Sheet		of		Attorney Docket Number	SC11342ZP C01

U. S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
		Number -Kind Code ² (if known)				
T.D	AA	4,300,150	11/10/1981	Colak		
	AB	5,523,601	06/04/1996	Yanagigawa		
	AC	5,539,238	06/23/1996	Malhi		
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	AE	5,801,431	09/01/1998	Ranjan		
	AF	6,025,231	02/15/2000	Hutter <i>et al.</i>		
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Examine r Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³	Number ⁴ Kind Code ² (if known)				
T-D	AI	EP	0 295 391 A1	04/21/1988	Eklund		
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T-D	AK	DE	195 35 140 A1	03/28/1996	Kitamura <i>et al.</i>		

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
T.D	AL	Bergemont <i>et al.</i> , "High Voltage Driver Built in a Low Voltage 0.18 μ m CMOS for Cache Redundancy Applications in Microprocessors," <i>ISPSD</i> , May 22-25, 2000, Toulouse, France.	
T.D	AM	Kim <i>et al.</i> , "A 650V rated RESURF-type LDMOS Employing an Internal Clamping Diode for Bulk Breakdown without EPI Layer," <i>Proceedings of 2001 International Symposium on Power Devices and ICs</i> , Osaka, Japan, 4-7 June 2001, p. 347-350.	
T.D	AN	PCT/US02/18353 PCT Search Report mailed 15 April 2003.	

Examiner Signature	<i>E. Mung Dang</i>	Date Considered	8/17/04
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation, if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English Language Translation is attached.

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